Vishay Semiconductors

Hyperfast Rectifier, 3 A FRED Pt[®]



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SMC (DO-214AB)

LINKS TO ADDITIONAL RESOURCES



| PRIMARY CHARACTERISTICS | | | | | |
|----------------------------------|----------------|--|--|--|--|
| I _{F(AV)} | 3 A | | | | |
| V _R | 100 V | | | | |
| V _F at I _F | 0.69 V | | | | |
| t _{rr} | 25 ns | | | | |
| T _J max. | 175 °C | | | | |
| Package | SMC (DO-214AB) | | | | |
| Circuit configuration | Single | | | | |

FEATURES

- Hyperfast recovery time, reduced Q_{rr}, and soft recovery
- °C maximum 175 operating junction temperature
- · Specified for output and snubber operation
- · Low forward voltage drop
- Low leakage current
- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C
- AEC-Q101 qualified, meets JESD 201 class 2 whisker test
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

DESCRIPTION / APPLICATIONS

State of the art hyperfast recovery rectifiers specifically designed with optimized performance of forward voltage drop and hyperfast recovery time.

The planar structure and the platinum doped life time control guarantee the best overall performance, ruggedness, and reliability characteristics.

These devices are intended for use in snubber, boost, lighting, piezo-injection, as high frequency rectifiers, and freewheeling diodes.

The extremely optimized stored charge and low recovery current minimize the switching losses and reduce power dissipation in the switching element.

MECHANICAL DATA

Case: SMC (DO-214AB)

Molding compound meets UL 94 V-0 flammability rating

Terminals: matte tin plated leads, solderable per J-STD-002

Polarity: color band denotes cathode end

| ABSOLUTE MAXIMUM RATINGS | | | | | | |
|---|-----------------------------------|--|-------------|-------|--|--|
| PARAMETER | SYMBOL | TEST CONDITIONS | VALUES | UNITS | | |
| Peak repetitive reverse voltage | V _{RRM} | | 100 | V | | |
| Average rectified forward current | I _{F(AV)} | T _{Sp} = 142 °C | 3 | Δ | | |
| Non-repetitive peak surge current | I _{FSM} | $T_J = 25 \ ^{\circ}C$, 6 ms square pulse | 130 | A | | |
| Operating junction and storage temperatures | T _J , T _{Stg} | | -55 to +175 | °C | | |

| ELECTRICAL SPECIFICATIONS (T _J = 25 $^{\circ}$ C unless otherwise specified) | | | | | | | |
|--|-----------------|---|------|------|------|-------|--|
| PARAMETER | SYMBOL | TEST CONDITIONS | MIN. | TYP. | MAX. | UNITS | |
| Breakdown voltage, blocking voltage | V_{BR}, V_{R} | I _R = 100 μA | 100 | - | - | | |
| Forward voltage, per diode | V _F | I _F = 3 A | - | 0.83 | 0.90 | V | |
| | | I _F = 3 A, T _J = 125 °C | - | 0.69 | 0.75 | | |
| Reverse leakage current, per diode | I_ | V _R = V _R rated | - | - | 2 | μA | |
| neverse leakage current, per diode | I _R | $T_J = 125 \text{ °C}, V_R = V_R \text{ rated}$ | - | 1 | 10 | μΑ | |
| Junction capacitance | CT | V _R = 100 V | - | 23 | - | pF | |

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1

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RoHS

COMPLIANT HALOGEN

FREE



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| DYNAMIC RECOVERY CHARACTERISTICS (T _J = 25 °C unless otherwise specified) | | | | | | | | |
|---|-----------------|--|--|------|------|------|-------|----|
| PARAMETER | SYMBOL | TEST CO | NDITIONS | MIN. | TYP. | MAX. | UNITS | |
| | | $I_F = 1 \text{ A}, \text{ d}I_F/\text{d}t = 50$ | A/ μ s, V _R = 30 V | - | 27 | - | | |
| Boyoroo rocoyory timo | + | I _F = 0.5 A, I _R = 1 A, | I _{rr} = 0.25 A | - | - | 25 | ns | |
| Reverse recovery time | t _{rr} | T _J = 25 °C | | - | 18 | - | | |
| | | T _J = 125 °C | I _F = 3 A, dI _F /dt = 200 A/µs, V _B = 100 V | - | 30 | - | | |
| Poole recovery ourrent | | T _J = 25 °C | | - | 2.1 | - | | |
| Peak recovery current | IRRM | T _J = 125 °C | | - | 4 | - | A | |
| Poverse recevery charge | Q _{rr} | T _J = 25 °C | VH - 100 V | - | 19 | - | nC | |
| Reverse recovery charge | | Q _{rr} | T _J = 125 °C | | - | 60 | - | nC |

| THERMAL - MECHANICAL SPECIFICATIONS | | | | | | | |
|--|-----------------------------------|---|------|-------|------|-------|--|
| PARAMETER | SYMBOL | TEST CONDITIONS | MIN. | TYP. | MAX. | UNITS | |
| Maximum junction and storage temperature range | T _J , T _{Stg} | | -55 | - | 175 | °C | |
| Thermal resistance, junction to mount | R _{thJM} | Device mounted on PCB with 2 x 3.5 mm soldering lands | - | 7.7 | 14 | °C/W | |
| Approximate weight | | | | 0.24 | | g | |
| Approximate weight | | | | 0.008 | | oz. | |
| Marking device | | Case style SMC (DO-214AB) | | 31 | -11 | | |

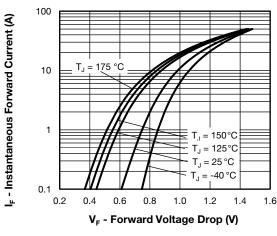


Fig. 1 - Typical Forward Voltage Drop Characteristics

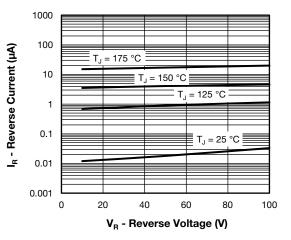
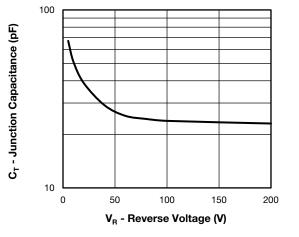


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage



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Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

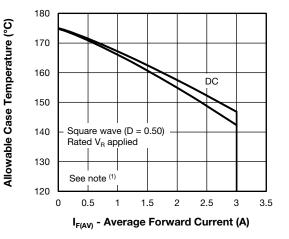


Fig. 4 - Maximum Allowable Case Temperature vs. Average Forward Current

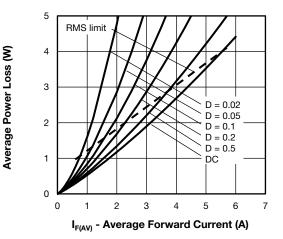


Fig. 5 - Forward Power Loss Characteristics

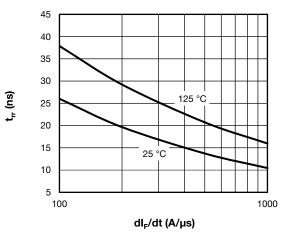
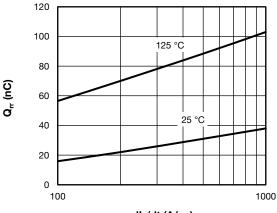


Fig. 6 - Typical Reverse Recovery Time vs. dI_F/dt



dl_F/dt (A/µs)

Fig. 7 - Typical Stored Charge vs. dl_F/dt

Note

⁽¹⁾ Formula used: $T_C = T_J - (Pd + Pd_{REV}) \times R_{thJC}$;

 $\begin{array}{l} \mathsf{Pd} = \mathsf{forward} \ \mathsf{power} \ \mathsf{loss} = \mathsf{I}_{\mathsf{F}(\mathsf{AV})} \times \mathsf{V}_{\mathsf{FM}} \ \mathsf{at} \ (\mathsf{I}_{\mathsf{F}(\mathsf{AV})}/\mathsf{D}) \ (\mathsf{see} \ \mathsf{fig.} \ 5); \\ \mathsf{Pd}_{\mathsf{REV}} = \mathsf{inverse} \ \mathsf{power} \ \mathsf{loss} = \mathsf{V}_{\mathsf{R1}} \times \mathsf{I}_{\mathsf{R}} \ (\mathsf{1} - \mathsf{D}); \ \mathsf{I}_{\mathsf{R}} \ \mathsf{at} \ \mathsf{V}_{\mathsf{R1}} = \mathsf{rated} \ \mathsf{V}_{\mathsf{R}} \end{array}$

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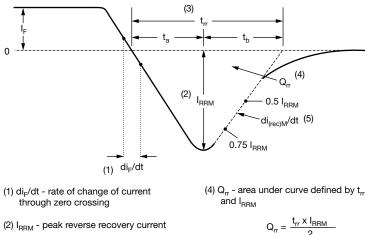
3

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VS-3ECH01HM3

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(3) $t_{\rm rr}$ - reverse recovery time measured from zero crossing point of negative going I_F to point where a line passing through 0.75 I_{RRM} and 0.50 I_{RRM} extrapolated to zero current.

(5) $di_{(rec)M}/dt$ - peak rate of change of current during t_b portion of t_{rr}

Fig. 8 - Reverse Recovery Waveform and Definitions

ORDERING INFORMATION TABLE

SHAY

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| Device code | VS- | 3 | Е | с | Н | 01 | н | М3 |
|-------------|-----|--------|---|-----------------------|---|---------|---------|---------|
| | 1 | 2 | 3 | 4 | 5 | 6 | 7 | 8 |
| | | | - | niconduo le (3 = 3 | • | oduct | | |
| | | - Circ | cuit conf | iguratior | - | | | |
| | 4 | | single o SMC p | | | | | |
| | 5 | | Process type, H = hyperfast recovery | | | | | |
| | | | Voltage code (01 = 100 V) | | | | | |
| | | | | 101 qua en-free, | | comolia | nt and | termina |
| | 0 | - 1010 | - naiog | en-nee, | | compila | nt, and | termine |

| ORDERING INFORMATION (Example) | | | | | | | | |
|--------------------------------|--|------|-----------------------------------|--|--|--|--|--|
| PREFERRED P/N | PREFERRED P/N QUANTITY PER REEL MINIMUM ORDER QUANTITY PACKAGING DESCRIPTION | | | | | | | |
| VS-3ECH01HM3/9AT | 3500 | 3500 | 13"diameter plastic tape and reel | | | | | |

| LINKS TO RELATED DOCUMENTS | | | | | |
|----------------------------|--------------------------|--|--|--|--|
| Dimensions | www.vishay.com/doc?95402 | | | | |
| Part marking information | www.vishay.com/doc?95472 | | | | |
| Packaging information | www.vishay.com/doc?95404 | | | | |

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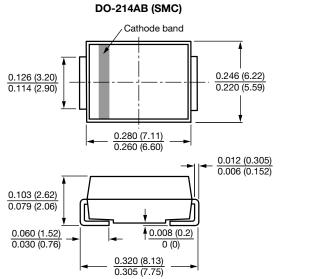


Outline Dimensions

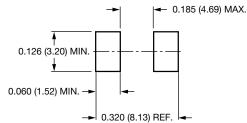
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DIMENSIONS in inches (millimeters)



Mounting Pad Layout



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